

**TRANSLATION**

**PATENT COOPERATION TREATY**

**PCT**

**INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY**

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference <b>P37020-P0</b>	<b>FOR FURTHER ACTION</b>	See Form PCT/IPEA/416
International application No. <b>PCT/JP2004/017622</b>	International filing date ( <i>day/month/year</i> ) <b>26.11.2004</b>	Priority date ( <i>day/month/year</i> ) <b>01.12.2003</b>
International Patent Classification (IPC) or national classification and IPC <b>H01L21/3065</b>		
Applicant <b>MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.</b>		

1. This report is the international preliminary examination report, established by this International Preliminary Examining Authority under Article 35 and transmitted to the applicant according to Article 36.
2. This REPORT consists of a total of <u>6</u> sheets, including this cover sheet.
3. This report is also accompanied by ANNEXES, comprising: a. <input checked="" type="checkbox"/> ( <i>sent to the applicant and to the International Bureau</i> ) a total of <u>3</u> sheets, as follows: <input checked="" type="checkbox"/> sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications authorized by this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions). <input type="checkbox"/> sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the Supplemental Box. b. <input type="checkbox"/> ( <i>sent to the International Bureau only</i> ) a total of (indicate type and number of electronic carrier(s)) _____, containing a sequence listing and/or tables related thereto, in computer readable form only, as indicated in the Supplemental Box Relating to Sequence Listing (see Section 802 of the Administrative Instructions).
4. This report contains indications relating to the following items: <input checked="" type="checkbox"/> Box No. I Basis of the report <input type="checkbox"/> Box No. II Priority <input type="checkbox"/> Box No. III Non-establishment of opinion with regard to novelty, inventive step and industrial applicability <input type="checkbox"/> Box No. IV Lack of unity of invention <input checked="" type="checkbox"/> Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement <input type="checkbox"/> Box No. VI Certain documents cited <input type="checkbox"/> Box No. VII Certain defects in the international application <input type="checkbox"/> Box No. VIII Certain observations on the international application

Date of submission of the demand	Date of completion of this report
Name and mailing address of the IPEA/JP	Authorized officer
Facsimile No.	Telephone No.

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## Box No. I Basis of the report

1. With regard to the **language**, this report is based on the international application in the language in which it was filed, unless otherwise indicated under this item.
- ☐ This report is based on translations from the original language into the following language \_\_\_\_\_, which is the language of a translation furnished for the purposes of:
- ☐ international search (Rule 12.3 and 23.1(b))
- ☐ publication of the international application (Rule 12.4)
- ☐ international preliminary examination (Rule 55.2 and/or 55.3)
2. With regard to the **elements** of the international application, this report is based on *(replacement sheets which have been furnished to the receiving Office in response to an invitation under Article 14 are referred to in this report as "originally filed" and are not annexed to this report)*:
- ☐ the international application as originally filed/furnished
- ☒ the description:
- pages 1-16 as originally filed/furnished
- pages\* \_\_\_\_\_ received by this Authority on \_\_\_\_\_
- pages\* \_\_\_\_\_ received by this Authority on \_\_\_\_\_
- ☒ the claims:
- nos. 2-8, 10-12, 14, 16-19 as originally filed/furnished
- nos.\* \_\_\_\_\_ as amended (together with any statement) under Article 19
- nos.\* 1, 9, 15 received by this Authority on 29.09.2005
- nos.\* \_\_\_\_\_ received by this Authority on \_\_\_\_\_
- ☒ the drawings:
- sheets 1-7 as originally filed/furnished
- sheets\* \_\_\_\_\_ received by this Authority on \_\_\_\_\_
- sheets\* \_\_\_\_\_ received by this Authority on \_\_\_\_\_
- ☐ a sequence listing and/or any related table(s) – see Supplemental Box Relating to Sequence Listing.
3. ☒ The amendments have resulted in the cancellation of:
- ☐ the description, pages \_\_\_\_\_
- ☒ the claims, nos. 13
- ☐ the drawings, sheets/figs \_\_\_\_\_
- ☐ the sequence listing (*specify*): \_\_\_\_\_
- ☐ any table(s) related to sequence listing (*specify*): \_\_\_\_\_
4. ☐ This report has been established as if (some of) the amendments annexed to this report and listed below had not been made, since they have been considered to go beyond the disclosure as filed, as indicated in the Supplemental Box (Rule 70.2(c)).
- ☐ the description, pages \_\_\_\_\_
- ☐ the claims, nos. \_\_\_\_\_
- ☐ the drawings, sheets/figs \_\_\_\_\_
- ☐ the sequence listing (*specify*): \_\_\_\_\_
- ☐ any table(s) related to sequence listing (*specify*): \_\_\_\_\_

\* If item 4 applies, some or all of those sheets may be marked "superseded."

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Box No. V	Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement		
1.	Statement		
	Novelty (N)	Claims <u>1-12, 14-19</u>	YES
		Claims _____	NO
	Inventive step (IS)	Claims _____	YES
		Claims <u>1-12, 14-19</u>	NO
	Industrial applicability (IA)	Claims <u>1-12, 14-19</u>	YES
		Claims _____	NO
2.	Citations and explanations (Rule 70.7)		
	<p>The following documents are cited in the international search report.</p> <p>Document 1: JP 2002-542623 A (Lam Research Corp.), 10 December 2002, paragraphs [0026] to [0033]</p> <p>Document 2: JP 2003-303812 A (Matsushita Electric Industrial Co., Ltd.), 24 October 2003, paragraph [0094] and fig. 1</p> <p>Document 3: JP 2000-299310 A (Denso Corp.), 24 October 2000, paragraphs [0063] to [0072] and fig. 7</p> <p>Document 4: WO 2003-030239 A1 (Sumitomo Precision Products Co., Ltd.), 10 April 2003, paragraph [0094] and fig. 1</p> <p>Document 5: JP 2001-284283 A (Hitachi, Ltd.), 12 October 2001, paragraph [0098]</p> <p>Claims 1 to 10, 18 and 19</p> <p>Document 1 discloses a method for plasma etching a silicon object within a processing chamber, wherein trenches are formed in the aforementioned silicon object by introducing an etching gas that contains O<sub>2</sub>, SF<sub>6</sub>, He or Cl<sub>2</sub> into the interior of the aforementioned processing chamber and then converting the aforementioned etching</p>		

Box No. V	Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement
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gas into a plasma by means of a TCP device.

Meanwhile, document 2 indicates that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device. Such being the case, it would have been obvious to a person skilled in the art to configure so that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device in the invention disclosed in document 1.

Furthermore, a person skilled in the art could set an appropriate frequency for the high-frequency power, regardless of the type of plasma etching gas that is used.

Such being the case, the inventions set forth in claims 1 to 10, 18 and 19 do not involve an inventive step.

Claims 11, 12 and 14

Document 1 discloses a method for plasma etching a silicon object within a processing chamber, wherein trenches are formed in the aforementioned silicon object by introducing an etching gas that contains O<sub>2</sub>, SF<sub>6</sub>, He or Cl<sub>2</sub> into the interior of the aforementioned processing chamber and then converting the aforementioned etching gas into a plasma by means of a TCP device.

Meanwhile, document 2 indicates that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device.

Furthermore, document 3 discloses a trench formation method wherein trenches are formed by means of SF<sub>6</sub> gas, and then a protective film is formed upon the side walls of the trenches by means of a gas that

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contains C<sub>4</sub>F<sub>8</sub>.

In addition, document 4 discloses a feature wherein trenches are formed by means of a gas system that contains SF<sub>6</sub> and C<sub>4</sub>F<sub>8</sub>, which is a gas for forming a protective film.

Documents 1, 3 and 4 all pertain to the same technical feature; i.e., forming trenches on a silicon substrate. Therefore, it is considered to have been easy for a person skilled in the art to conceive of forming trenches by means of the gas disclosed in document 1, which contains O<sub>2</sub>, SF<sub>6</sub>, He or Cl<sub>2</sub>, and then forming both trenches and protective films by means of the gas system disclosed in document 4, which contains SF<sub>6</sub> and C<sub>4</sub>F<sub>8</sub>, in the light of the disclosures in document 3.

Furthermore, in the light of the disclosure in document 2 it would have been obvious to a person skilled in the art to configure so that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device in the invention disclosed in document 1.

Such being the case, the inventions set forth in claims 11, 12 and 14 do not involve an inventive step.

Claims 15 to 17

Document 5 discloses a method for plasma etching a silicon object by means of Ar/CF<sub>4</sub>. Therein, it would have been easy for a person skilled in the art to conceive of increasing the precision of the etching depth by adjusting the flow rate of the Ar or the CF<sub>4</sub> and by using a gas other than CF<sub>4</sub> in order to decrease the etching speed.

Such being the case, the inventions set forth in

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claims 15 to 17 do not involve an inventive step.